

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

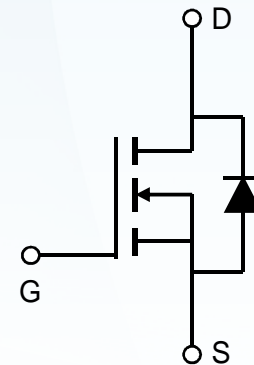
▶ Domestic	Part Number	AO4466
▶ Overseas	Part Number	AO4466
▶ Equivalent	Part Number	AO4466

EV is the abbreviation of name EVVO

N-Channel MOSFET

General Description

The AO4466 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.



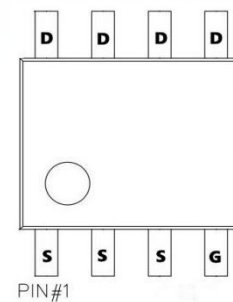
Product Summary

$$V_{DS} (V) = 30V$$

$$I_D = 10A$$

$$R_{DS(ON)} < 18m\Omega \quad (V_{GS} = 10V)$$

$$R_{DS(ON)} < 25m\Omega \quad (V_{GS} = 4.5V)$$



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{AF}	I_D	$T_A=25^\circ\text{C}$	10
		$T_A=70^\circ\text{C}$	7
Pulsed Drain Current ^B	I_{DM}	64	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.1
		$T_A=70^\circ\text{C}$	2
Avalanche Current ^{B, G}	I_{AR}	12	A
Repetitive avalanche energy 0.1mH ^{B, G}	E_{AR}	7	mJ
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	36	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	62	75
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	18	24	$^\circ\text{C/W}$

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Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	64			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =10A		13	18	mΩ
		V _{GS} =4.5V, I _D =5A		19	25	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3A		17		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.75	1	V
I _S	Maximum Body-Diode Continuous Current				2.4	A
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz	298	373	448	pF
C _{OSS}	Output Capacitance		46	67	88	pF
C _{rSS}	Reverse Transfer Capacitance		24	41	58	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.6	1.8	2.8	Ω
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =10A	5.7	7.1	8.6	nC
Q _{g(4.5V)}	Total Gate Charge		2.7	3.5	4.2	nC
Q _{gs}	Gate Source Charge			1.2		nC
Q _{gd}	Gate Drain Charge			1.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =1.5Ω, R _{GEN} =3Ω		4.3		ns
t _r	Turn-On Rise Time			2.8		ns
t _{D(off)}	Turn-Off DelayTime			15.8		ns
t _f	Turn-Off Fall Time			3		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =10A, dI/dt=100A/μs	8.4	10.5	12.6	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =10A, dI/dt=100A/μs	3.6	4.5	5.4	nC
t _{rr}	Body Diode Reverse Recovery Time	I _F =10A, dI/dt=500A/μs	4.7	6.0	7.2	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =10A, dI/dt=500A/μs	5.3	6.6	8	nC

A: The value of R_{θJA} is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s junction to ambient thermal resistance rating.

G: L=100uH, V_{DD}=0V, R_G=0Ω, rated V_{DS}=30V and V_{GS}=10V

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

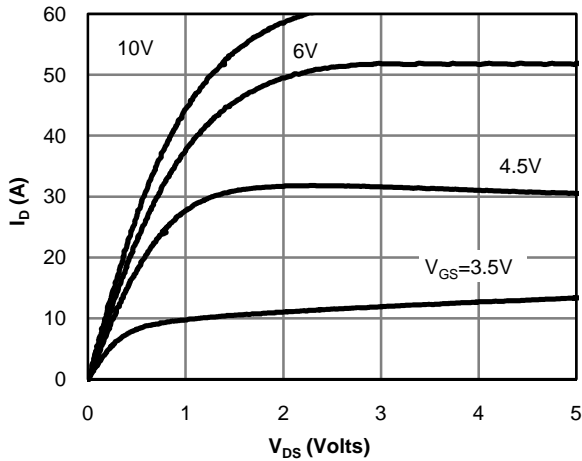


Fig 1: On-Region Characteristics

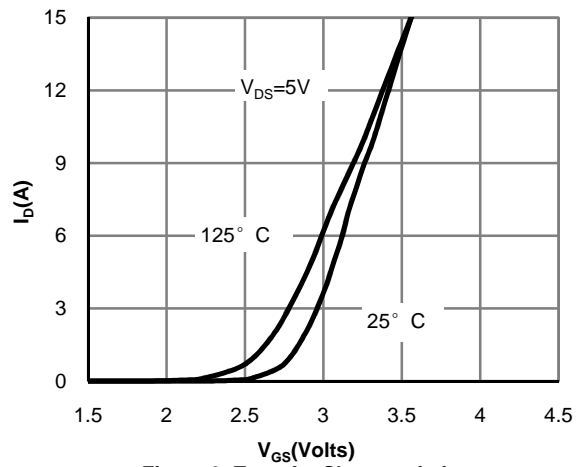


Figure 2: Transfer Characteristics

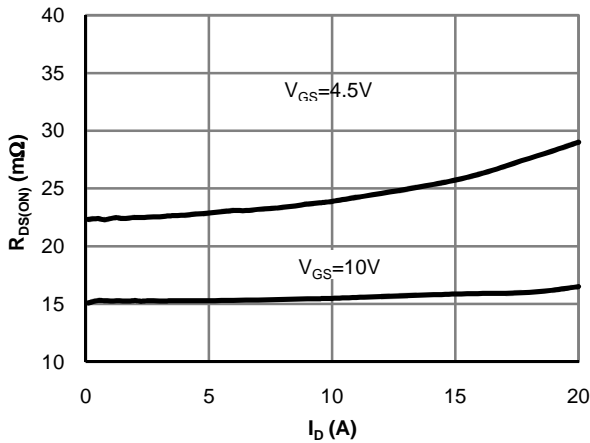


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

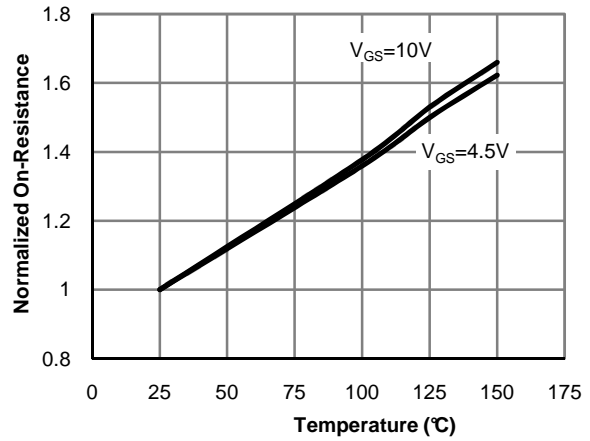


Figure 4: On-Resistance vs. Junction Temperature

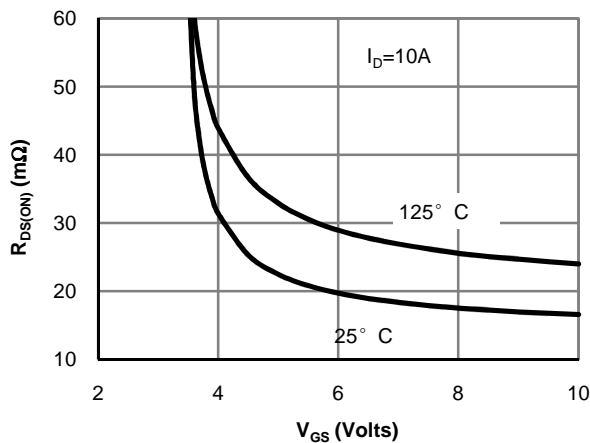


Figure 5: On-Resistance vs. Gate-Source Voltage

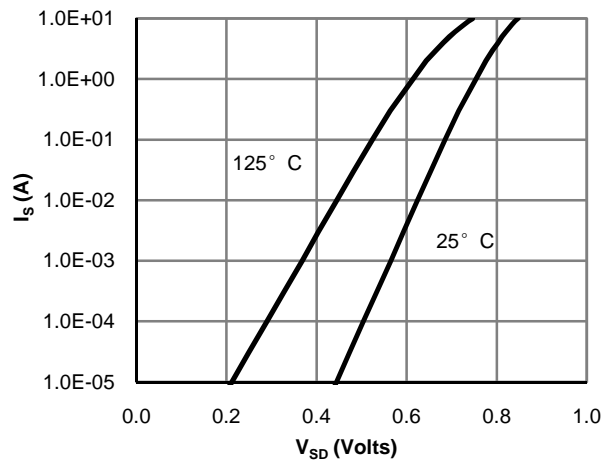


Figure 6: Body-Diode Characteristics

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

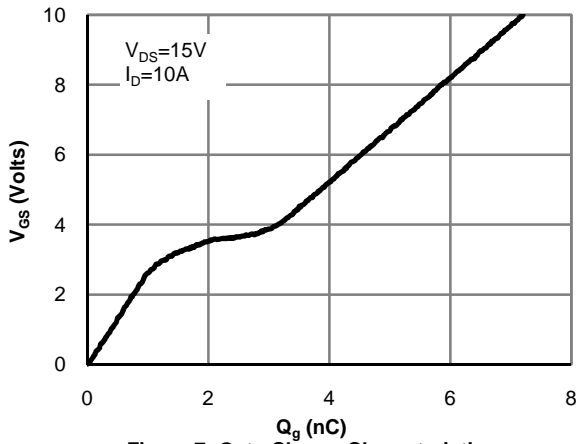


Figure 7: Gate-Charge Characteristics

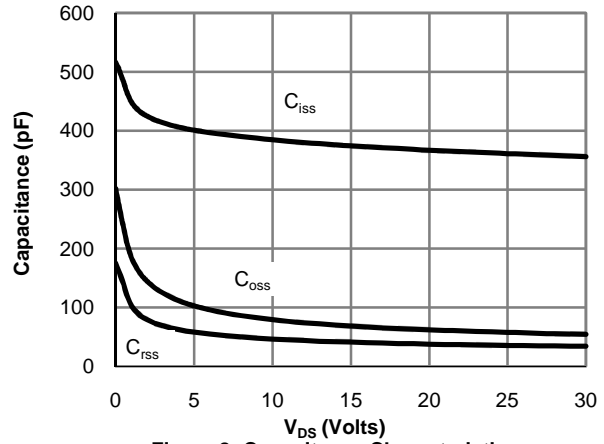


Figure 8: Capacitance Characteristics

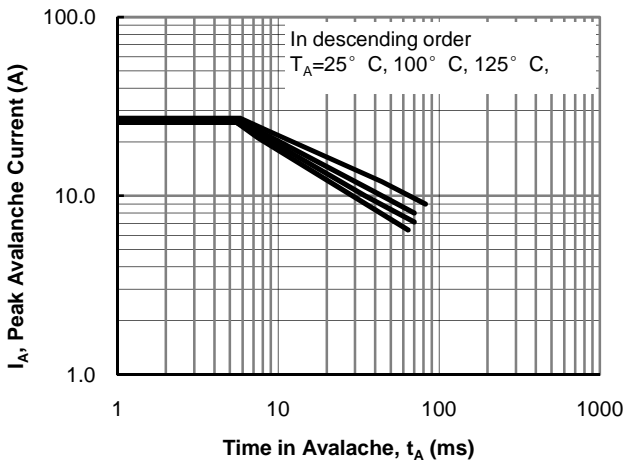


Figure 9: Single Pulse Avalanche Capability

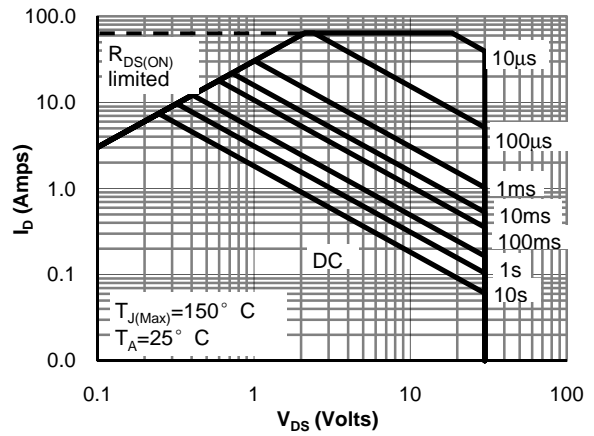


Figure 10: Maximum Forward Biased Safe Operating Area (Note E)

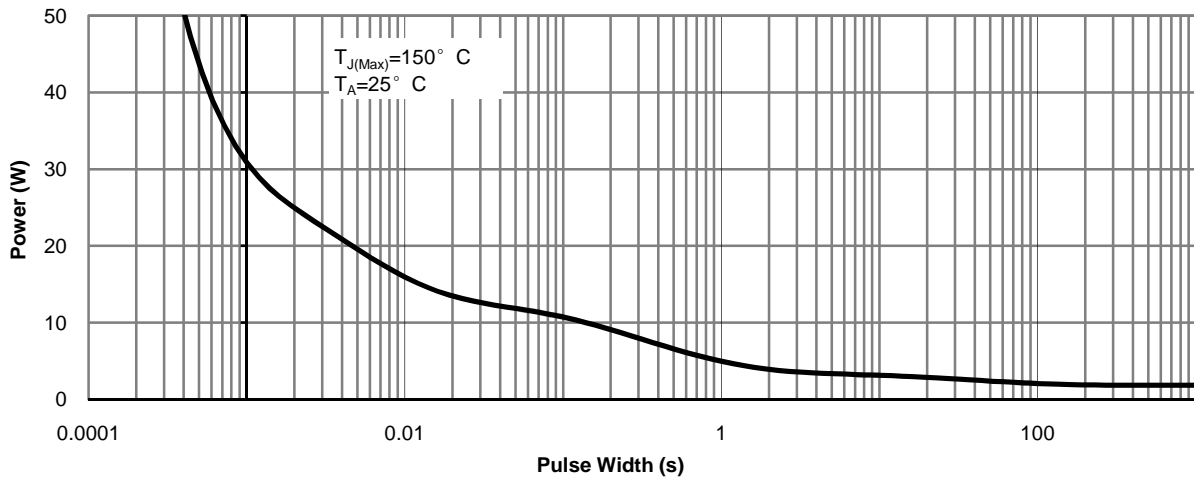
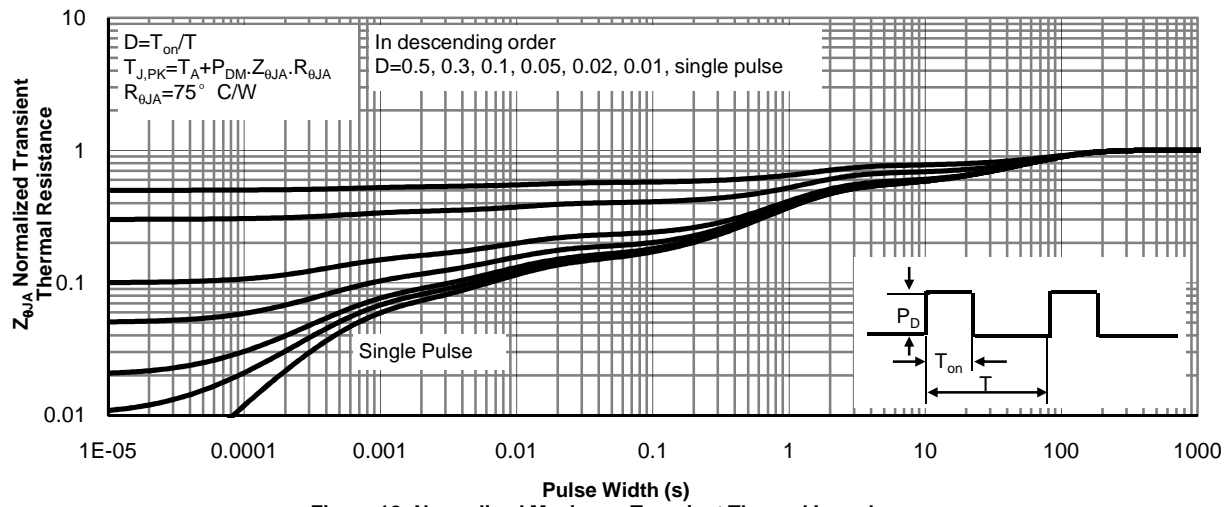


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note E)

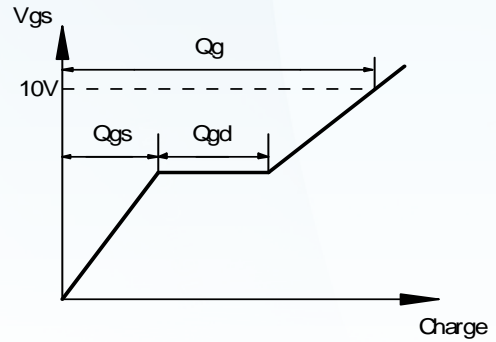
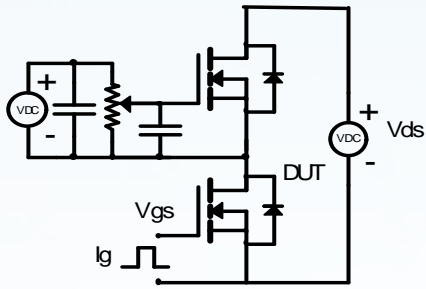
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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

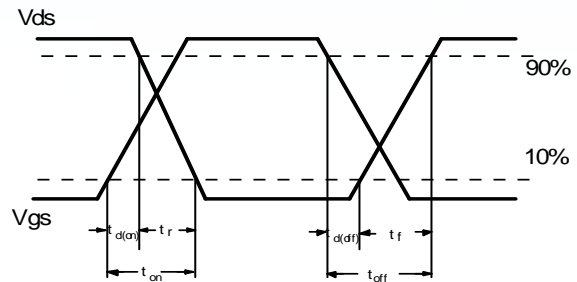
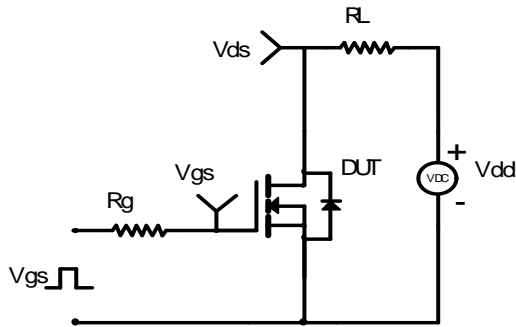


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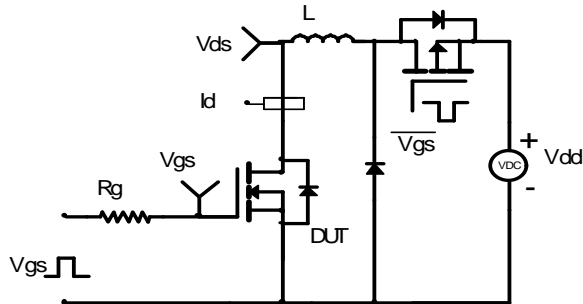
Gate Charge Test Circuit & Waveform



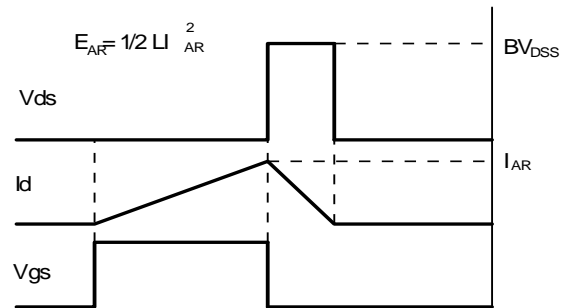
Resistive Switching Test Circuit & Waveforms



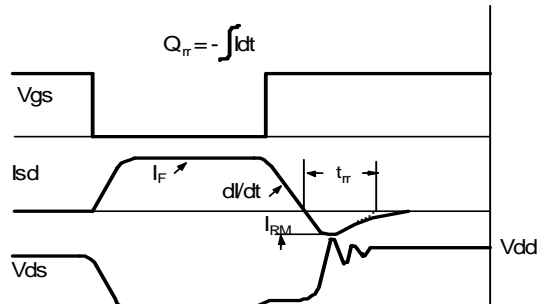
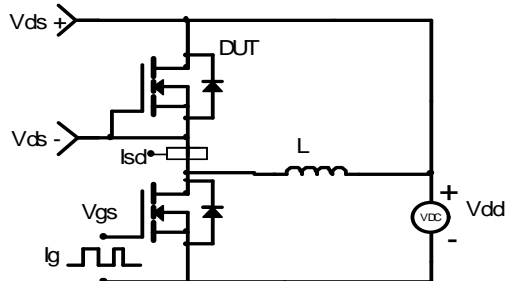
Unclamped Inductive Switching (UIS) Test Circuit &



Waveforms



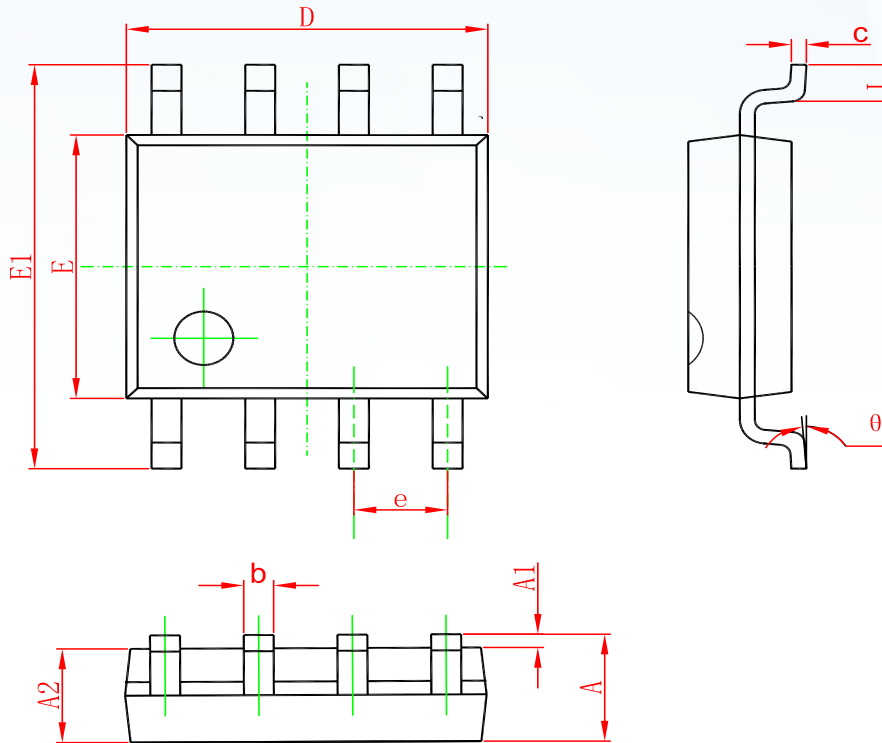
Diode Recovery Test Circuit & Waveforms



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PACKAGE OUTLINE DIMENSIONS

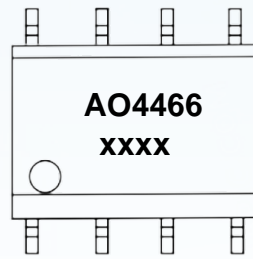
SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

N-Channel MOSFET

Marking



("xxxx"代表年份周期)

Ordering information

Order code	Package	Baseqty	Deliverymode
AO4466	SOP-8	3000	Tape and reel

Disclaimer

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